TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

2SC3421

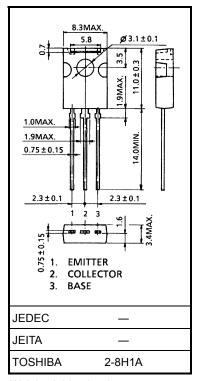
Audio Frequency Power Amplifier Applications

Unit: mm

- Complementary to 2SA1358
- Suitable for driver of 60 to 80 watts audio amplifier
- High breakdown voltage

Maximum Ratings (Tc = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V_{CBO}	120	V	
Collector-emitter voltage		V _{CEO}	120	V	
Emitter-base voltage		V _{EBO}	5	V	
Collector current		I _C	1	Α	
Base current		Ι _Β	100	mA	
Collector power dissipation	Ta = 25°C	Pc	1.5	W	
	Tc = 25°C	1 0	10		
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	−55 to 150	°C	



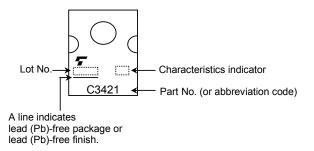
Weight: 0.82 g (typ.)

Electrical Characteristics (Tc = 25°C)

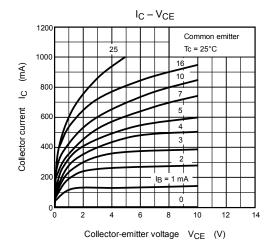
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 120 V, I _E = 0	_	_	100	nA
Emitter cut-off current	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	100	nA
Collector-emitter breakdown voltage	V (BR) CEO	I _C = 10 mA, I _B = 0	120	_	_	٧
DC current gain	h _{FE} (Note)	V _{CE} = 5 V, I _C = 100 mA	80	_	240	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = 500 mA, I _B = 50 mA	_	0.30	1.0	V
Base-emitter voltage	V _{BE}	V _{CE} = 5 V, I _C = 500 mA	_	0.78	1.0	V
Transition frequency	f _T	V _{CE} = 5 V, I _C = 100 mA	_	120	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	15	_	pF

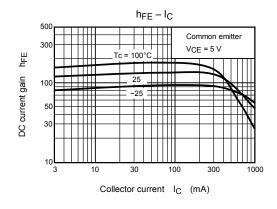
Note: hFE classification O: 80 to 160, Y: 120 to 240

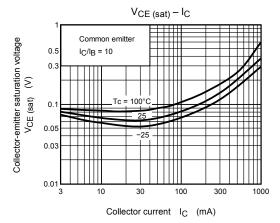
Marking

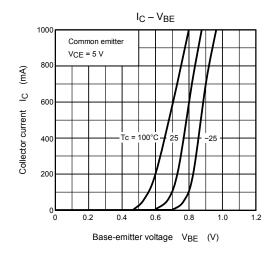


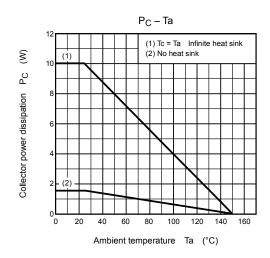
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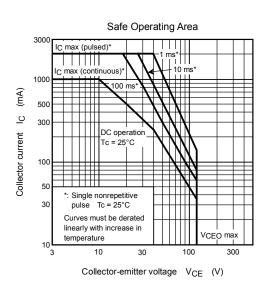












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